

## NCE N-Channel Enhancement Mode Power MOSFET

### Description

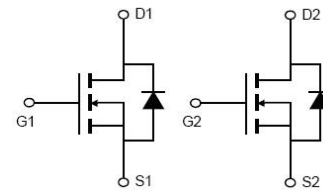
The NCE60ND03N uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other switching application.

### General Features

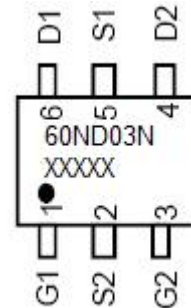
- $V_{DS} = 60V, I_D = 3A$   
 $R_{DS(ON)} < 84m\Omega @ V_{GS} = 10V$   
 $R_{DS(ON)} < 98.4m\Omega @ V_{GS} = 4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

### Application

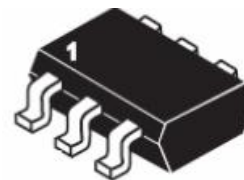
- Battery switch
- DC/DC converter



Schematic diagram



Marking and pin Assignment



SOT23-6L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
60ND03N	NCE60ND03N	SOT-23-6L	Ø330mm	12mm	3000 units

### Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	3	A
Drain Current-Pulsed (Note 1)	$I_{DM}$	10	A
Maximum Power Dissipation	$P_D$	1.7	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ\text{C}$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	73.5	$^\circ\text{C/W}$
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### Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

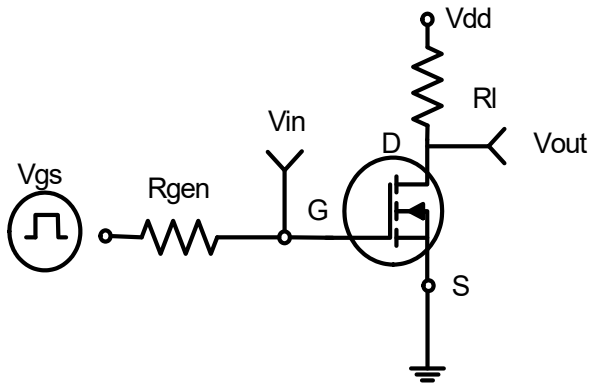
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						

Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60	65	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.8	1.3	2.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A	-	73	84	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	82	98.4	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =3A	4	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, F=1.0MHz	-	510	-	PF
Output Capacitance	C <sub>oss</sub>		-	34	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	26	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =3A V <sub>GS</sub> =10V, R <sub>GEN</sub> =1Ω	-	6	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	15	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V, I <sub>D</sub> =3A, V <sub>GS</sub> =10V	-	14.6	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.6	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =3A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	3	A

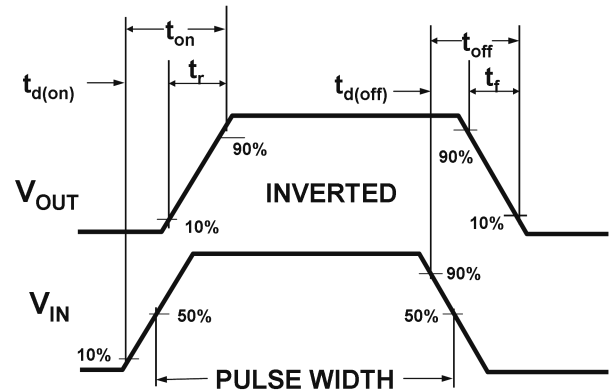
## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

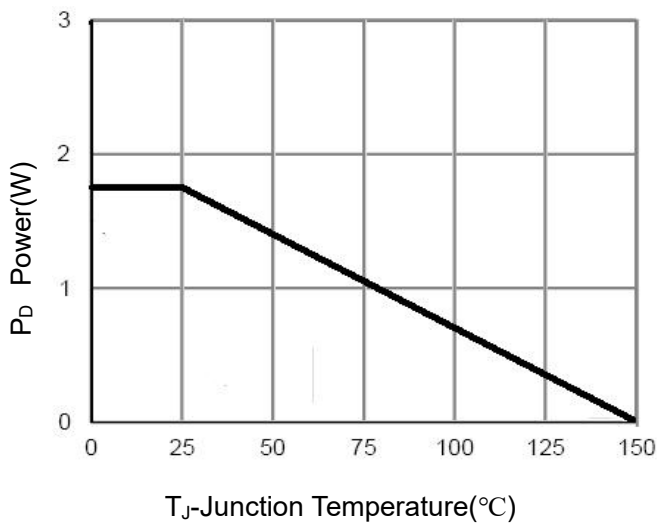
## Typical Electrical and Thermal Characteristics



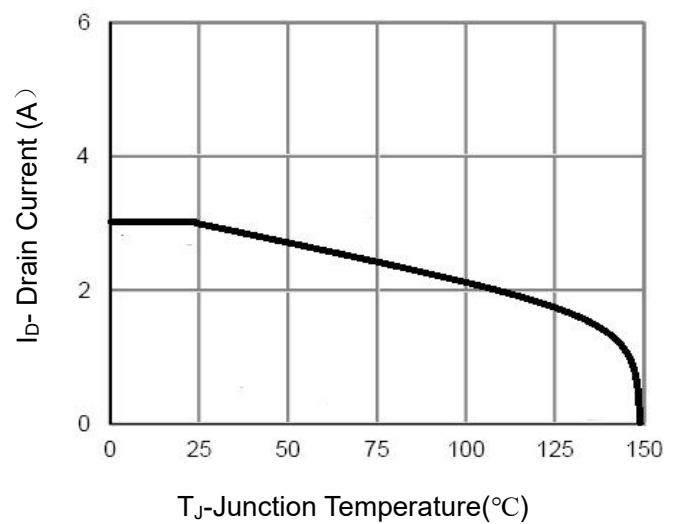
**Figure 1: Switching Test Circuit**



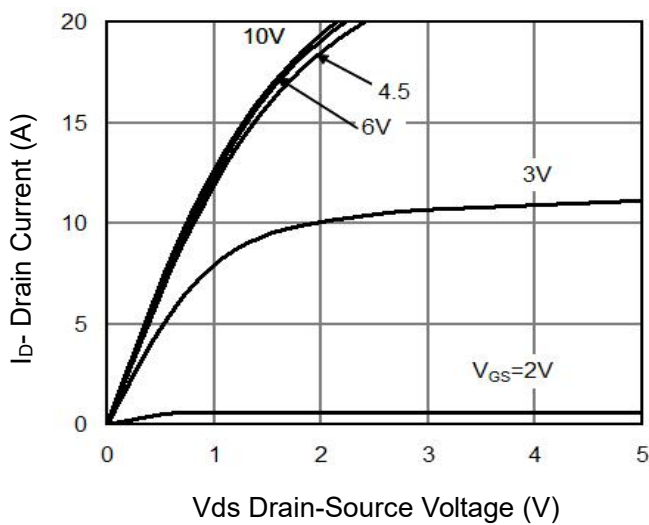
**Figure 2: Switching Waveforms**



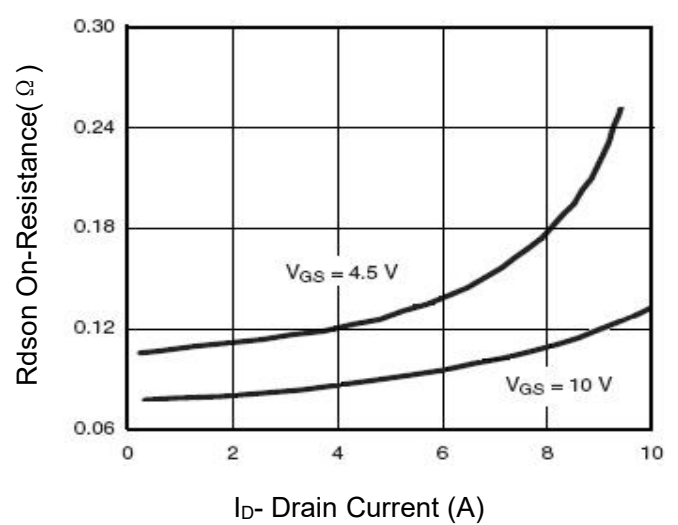
**Figure 3 Power Dissipation**



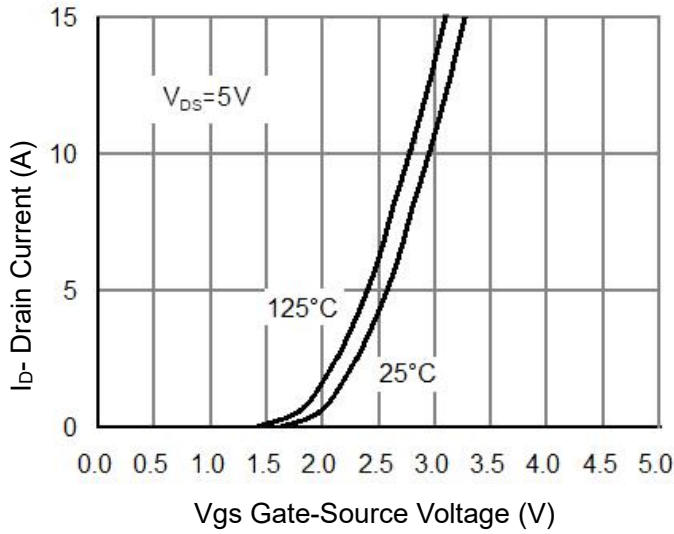
**Figure 4 Drain Current**



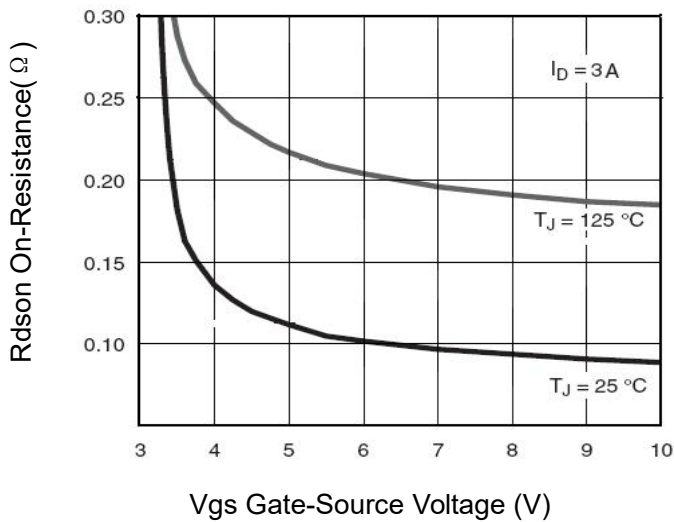
**Figure 5 Output Characteristics**



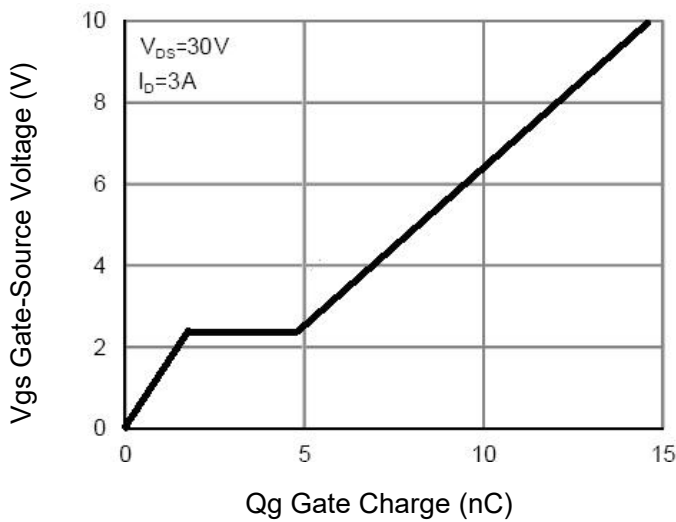
**Figure 6 Drain-Source On-Resistance**



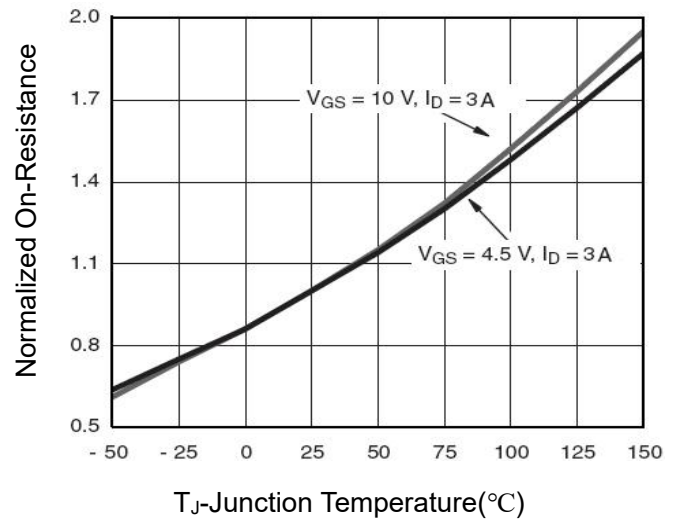
**Figure 7 Transfer Characteristics**



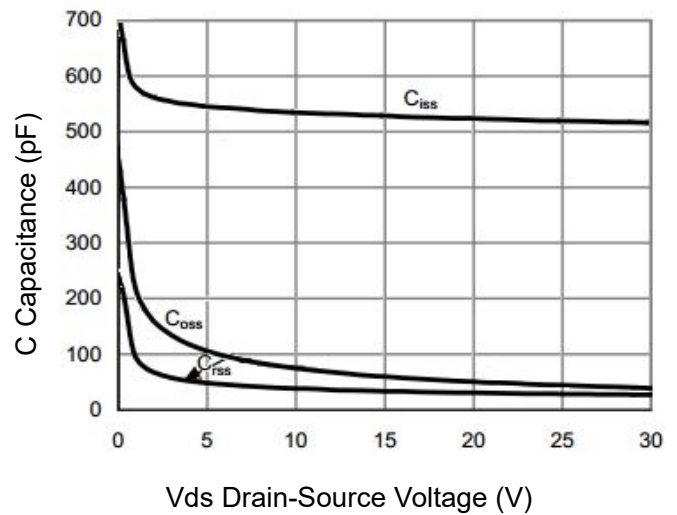
**Figure 9  $R_{DS(on)}$  vs  $V_{GS}$**



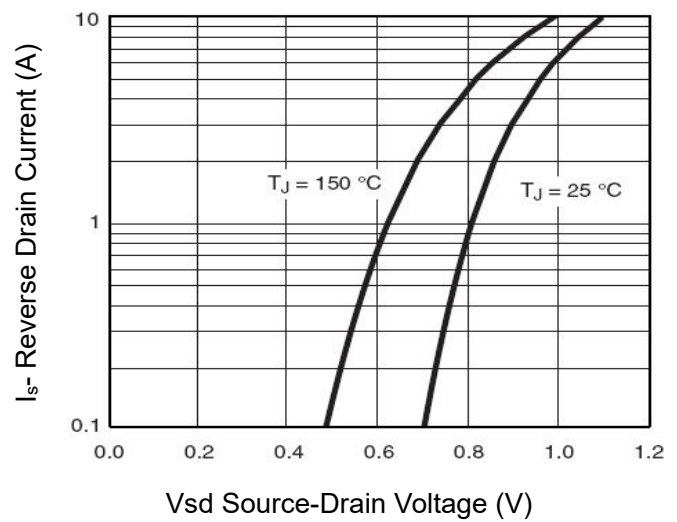
**Figure 11 Gate Charge**



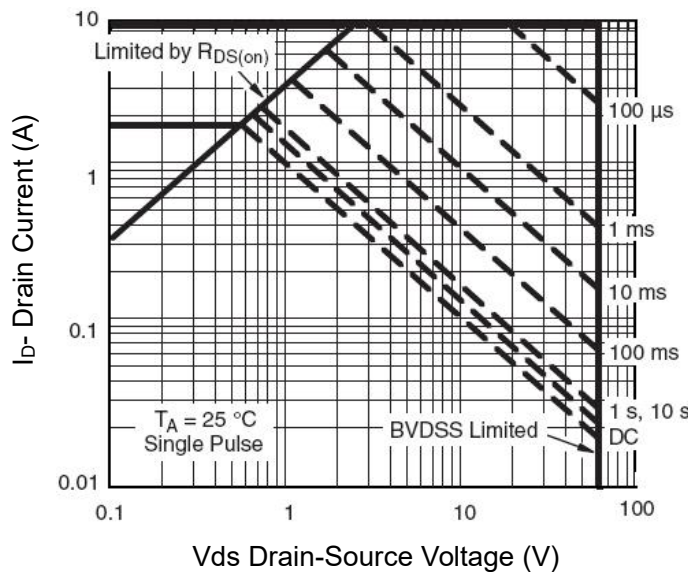
**Figure 8 Drain-Source On-Resistance**



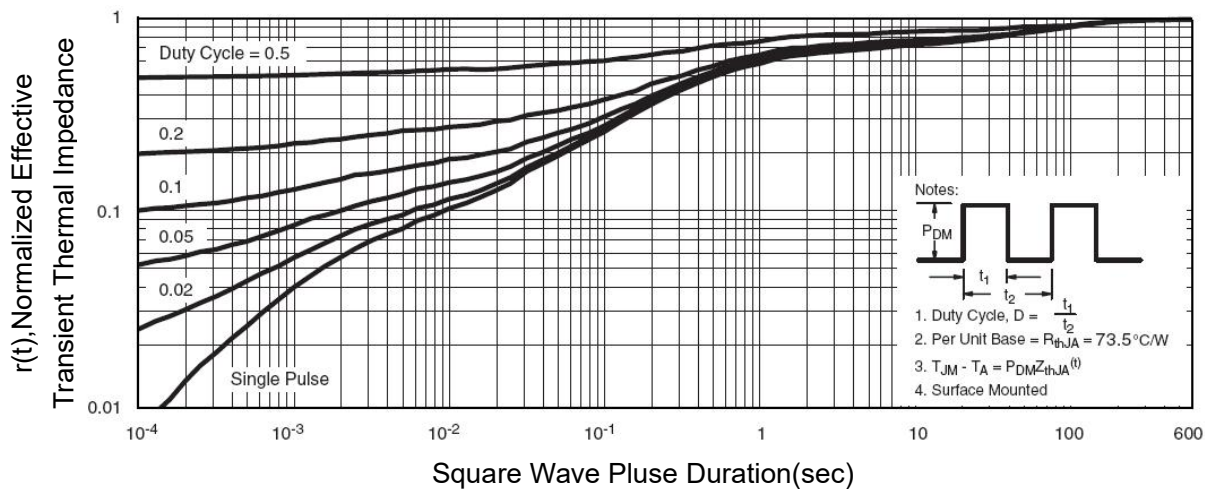
**Figure 10 Capacitance vs  $V_{DS}$**



**Figure 12 Source- Drain Diode Forward**

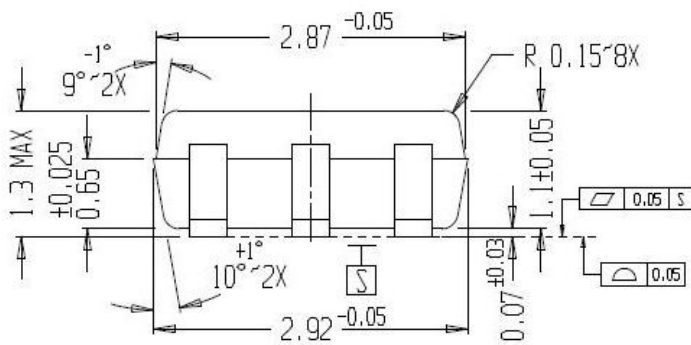
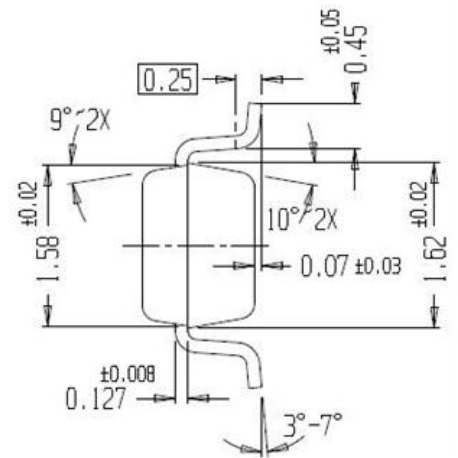
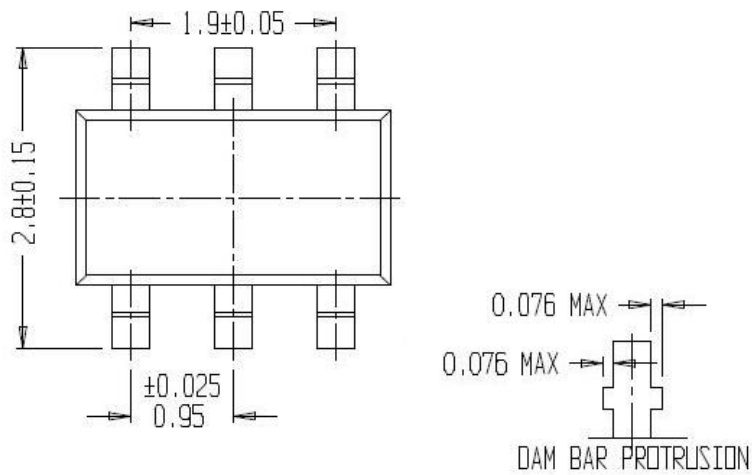


**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

## SOT-23-6L Package Information



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